

Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing

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Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

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Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

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Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature

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Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes

Kozlovski, Vitali V.; **Korolkov, Oleg;** Davydovskaja, Klavdia S.; Lebedev, Alexander A.; Levinšteĭn, Michael E.; **Sleptsuk, Natalja;** Strel'Chuk, Anatolii M.; **Toompuu, Jana** Technical Physics Letter 2020 / p. 287 - 289 <https://doi.org/10.1134/S1063785020030244> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

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SiC schottky diode rectifier bridge represented as the diffusion-welded stack

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